

isc Silicon NPN Power Transistor

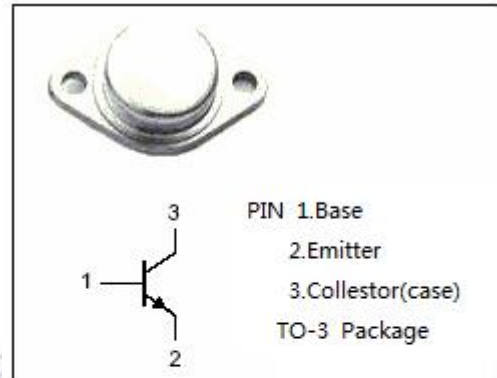
2SC1112

DESCRIPTION

- With TO-3 Package
- Wide area of safe operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

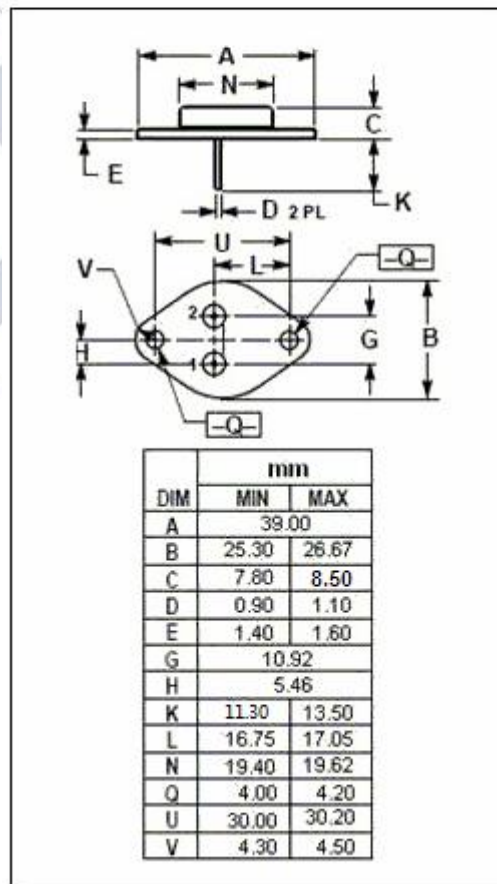
APPLICATIONS

- For audio frequency power amplifier applications



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	160	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	6	A
P _C	Collector Power Dissipation	50	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Power Transistor**2SC1112****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			2.0	V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	100			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	5			V
h _{FE}	DC Current Gain	I _C = 3.0A; V _{CE} = 4V	30		150	
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 12V; f _{test} = 1MHz	10			MHz

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